

### MMBD4148W SWITCHING DIODE

#### FEATURES

Power dissipation

$P_D$ : 200 mW ( $T_{amb}=25$  )

Collector current

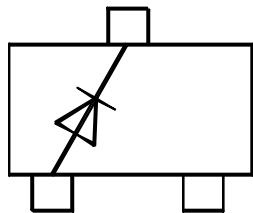
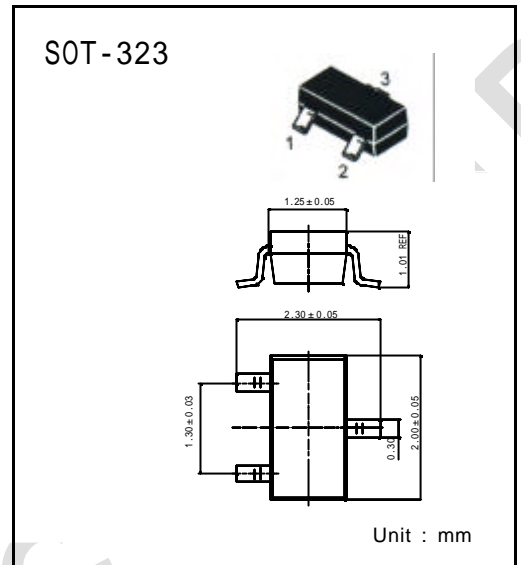
$I_o$  : 150 mA

Collector-base voltage

$V_R$  : 75 V

Operating and storage junction temperature range

$T_J, T_{stg}$ : -55 to +150



Marking A2、KA2、KT1

#### ELECTRICAL CHARACTERISTICS ( $T_{amb}=25$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)R}$	$I_R=100\mu A$	75		V
Reverse voltage leakage current	$I_R$	$V_R=75V$		1	$\mu A$
Forward voltage	$V_F$	$I_F=1mA$ $I_F=10mA$ $I_F=50mA$ $I_F=150mA$		0.715 0.855 1 1.25	V
Diode capacitance	$C_D$	$V_R=0V$ $f=1MHz$		2	pF
Reveres recovery time	$t_{rr}$	$I_F=I_R=10mA$ $I_{rr}=0.1 \times I_R$		4	nS

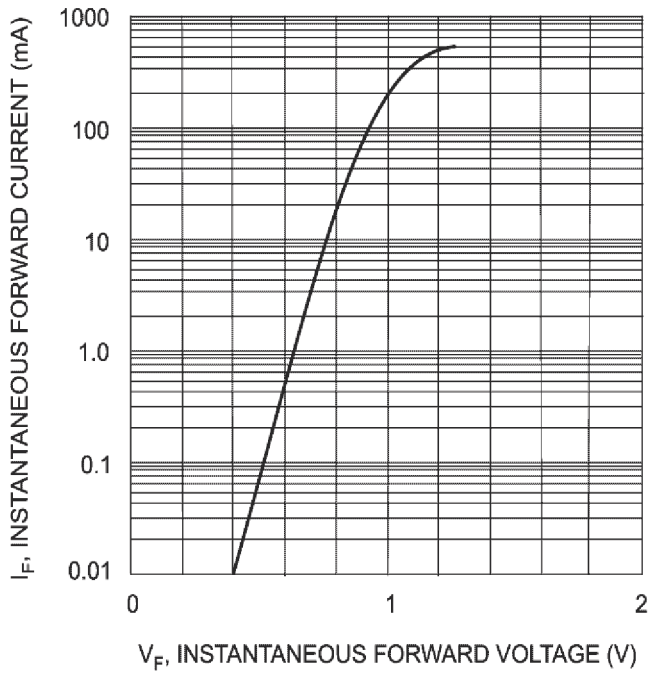


Fig. 1 Forward Characteristics

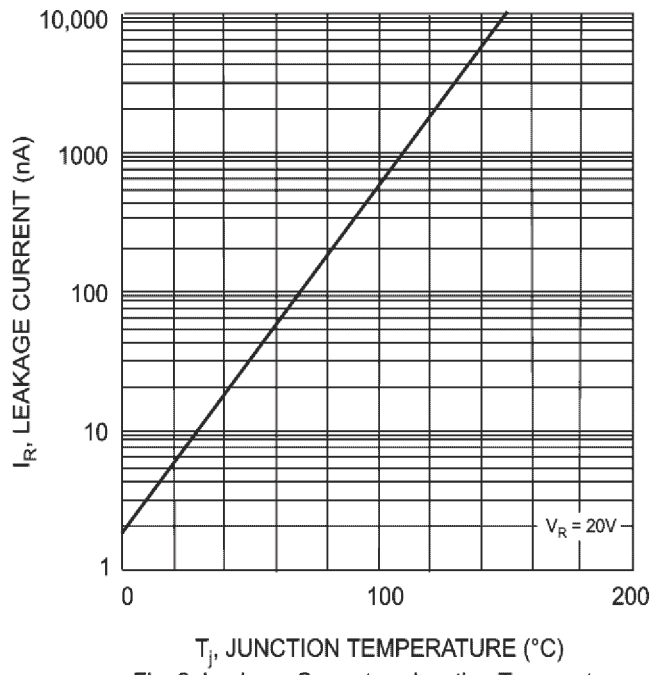
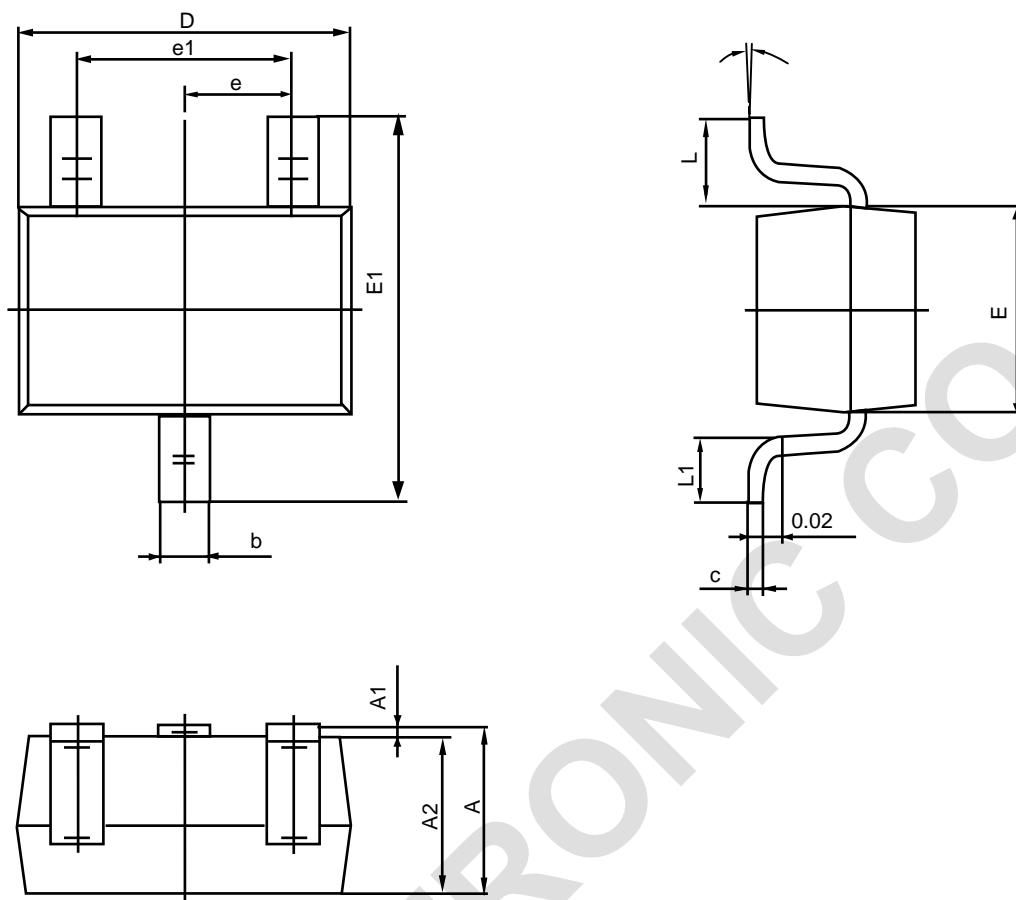


Fig. 2 Leakage Current vs Junction Temperature



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.200	0.400	0.008	0.016
c	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
e	0.650TYP		0.026TYP	
e1	1.200	1.400	0.047	0.055
L	0.525REF		0.021REF	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°